

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S11 1	1423	epitaxial\$3 near3 (gallium near nitride GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:31
S11 2	10307	(438/197,211,257,585,587,594,634, 637,672,675,251,261,597).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 08:32
S11 3	1525	((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film)) with (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:33
S11 4	1623	((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film)) with (gallium near nitride GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:36
S11 5	2300	(gallium near nitride GaN) near3 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:35
S11 6	250	((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film)) with S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 15:38
S11 7	187	passivat\$4 near5 traps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:36
S11 8	0	S116 with S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:36
S11 9	511	S116 and7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:37
S12 0	0	S116 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:37

S12 1	6	S116 and passivat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:43
S12 2	1	S121 and (silicon adj nitride SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 08:43
S12 3	187	passivat\$4 near5 traps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 15:37
S12 4	2	S123 and 'HEMT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 15:36
S12 5	324	passivat\$4 with traps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 15:37
S12 6	44	S125 and ((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 15:38
S12 7	324	passivat\$4 with traps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:35
S12 8	1965	257/194,e21.403,e21.407,e29. 246-e29.253.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:36
S12 9	567	438/162,172.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:37
S13 0	0	thermally near assisted and silicon adj nitride and passivat\$4 and traps and epitaxial and growth near chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/05 17:28

S13 2	25	thermally and assisted and silicon adj nitride and passivat\$4 and traps and epitaxial and growth and chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/05 17:30
S13 4	25	thermally and assisted and silicon adj nitride and passivat\$4 and traps and epitaxial and growth with chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/05 17:29
S13 5	25	thermally and assisted and silicon adj nitride and passivat\$4 and traps and epitaxial and chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/05 17:29
S13 6	25	thermally near3 assisted and silicon adj nitride and passivat\$4 and traps and epitaxial and growth and chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/05 17:30
S13 7	25	thermally near assisted and silicon adj nitride and passivat\$4 and traps and epitaxial and growth and chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/05 17:30
S13 8	0	(thermally near assisted with silicon adj nitride) and passivat\$4 and traps and epitaxial and growth and chamber and (after before).clm.	US-PGPUB	OR	OFF	2006/01/06 11:03
S13 9	189	passivat\$4 near5 traps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 11:03
S14 0	1966	257/194,e21.403,e21.407,e29. 246-e29.253.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 11:03
S14 1	2	S140 and S139	US-PGPUB	OR	OFF	2006/01/06 11:04
S14 2	2	S141 and passivat\$4	US-PGPUB	OR	OFF	2006/01/06 11:05
S14 3	10327	(438/197,211,257,585,587,594,634, 637,672,675,251,261,597).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 11:05
S14 4	3	S143 and S139	US-PGPUB	OR	OFF	2006/01/06 11:05